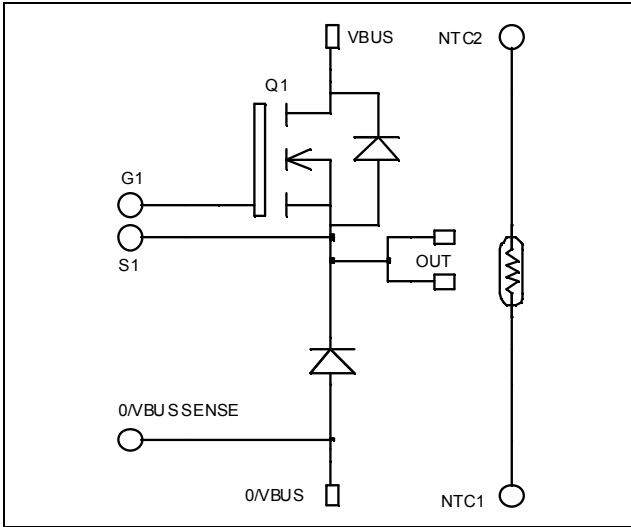


## Buck Chopper MOSFET Power Module

$V_{DSS} = 500V$   
 $R_{DSon} = 35m\Omega$  typ @  $T_j = 25^\circ C$   
 $I_D = 99A$  @  $T_c = 25^\circ C$



### Application

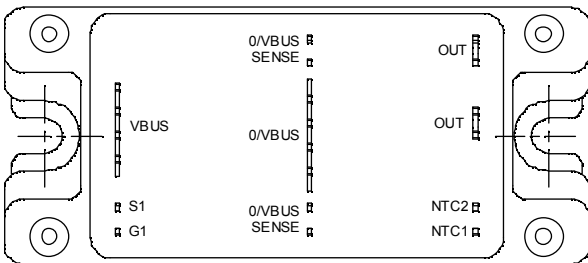
- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant



### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	500	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	99
		$T_c = 80^\circ C$	74
$I_{DM}$	Pulsed Drain current	396	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	39	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	781
$I_{AR}$	Avalanche current (repetitive and non repetitive)	51	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			200	$\mu\text{A}$
		$V_{GS} = 0V, V_{DS} = 400V$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 49.5A$		35	39	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$	3		5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 150$	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		14		nF
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		2.8		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.2		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 250V$ $I_D = 99A$		280		nC
$Q_{gs}$	Gate – Source Charge			80		
$Q_{gd}$	Gate – Drain Charge			140		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 99A$ $R_G = 1\Omega$		21		ns
$T_r$	Rise Time			38		
$T_{d(off)}$	Turn-off Delay Time			75		
$T_f$	Fall Time			93		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 99A, R_G = 1\Omega$		2070		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			1690		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 99A, R_G = 1\Omega$		3112		$\mu\text{J}$
$E_{off}$	Turn-off Switching Energy			2026		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		350	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		600	
$I_F$	DC Forward Current			120		A
$V_F$	Diode Forward Voltage	$I_F = 120A$		1.6	1.8	V
		$I_F = 240A$		1.9		
		$I_F = 120A$	$T_j = 125^\circ\text{C}$		1.4	
$t_{rr}$	Reverse Recovery Time	$I_F = 120A$ $V_R = 400V$ $di/dt = 400A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		130	ns
			$T_j = 125^\circ\text{C}$		170	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 120A$ $V_R = 400V$ $di/dt = 400A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		440	nC
			$T_j = 125^\circ\text{C}$		1840	

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	Transistor		0.16	°C/W	
		Diode		0.46		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

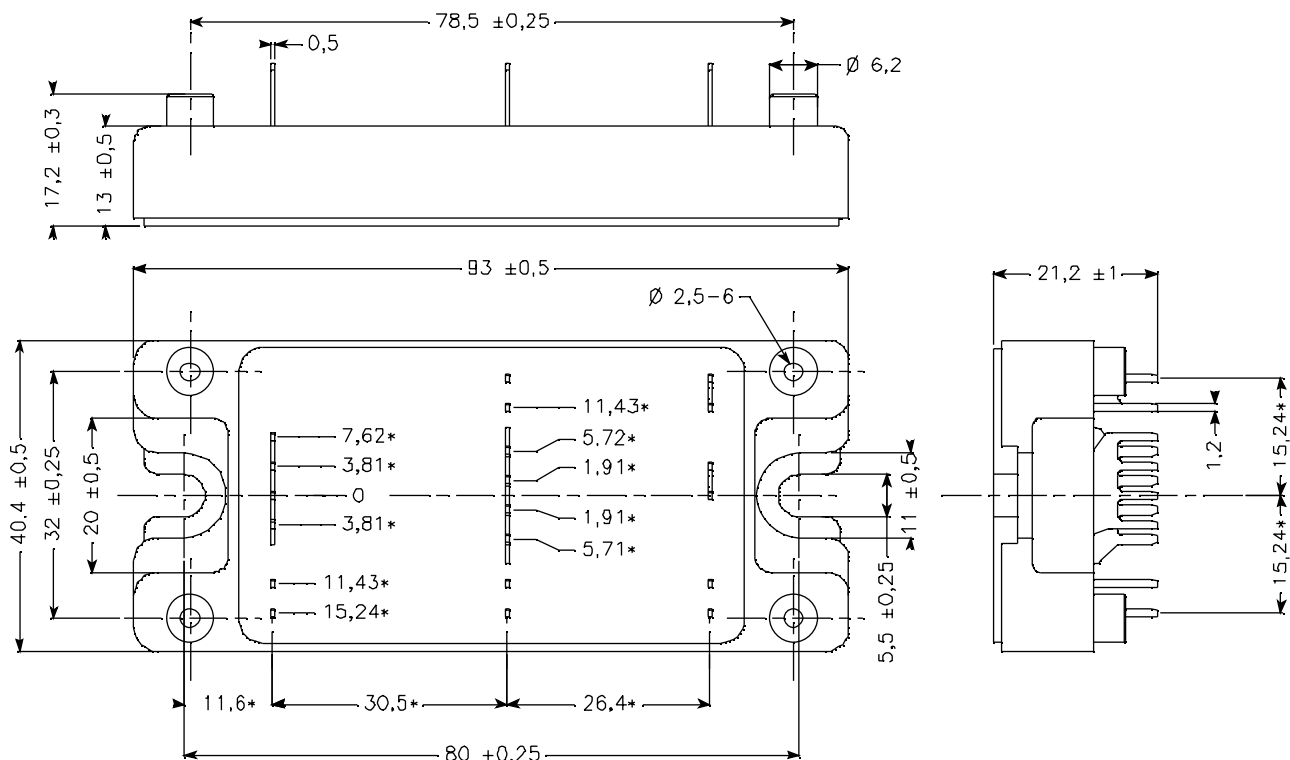
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

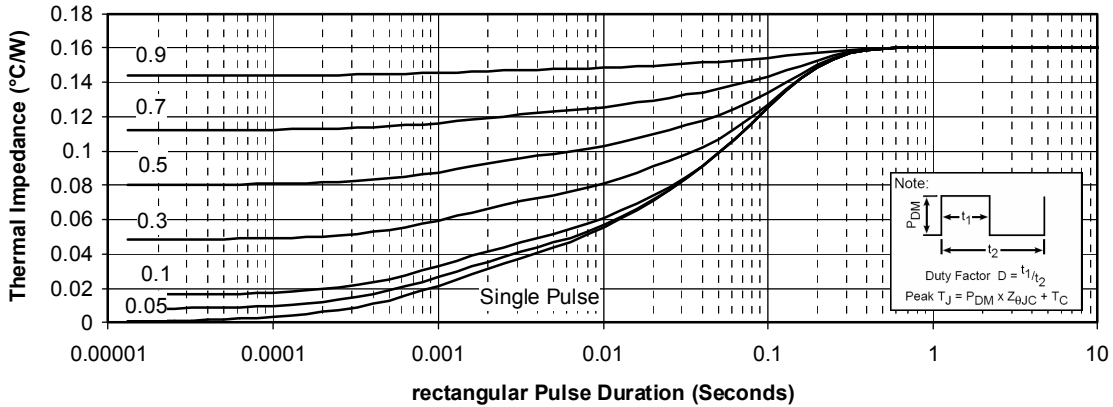
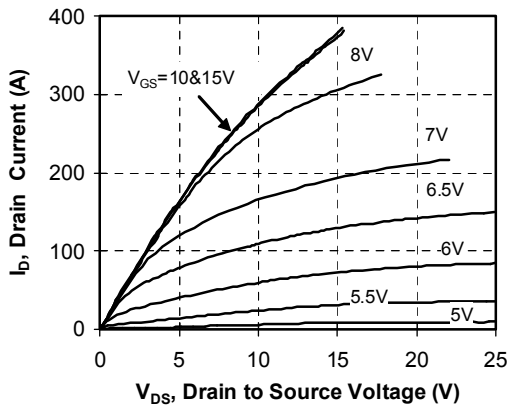
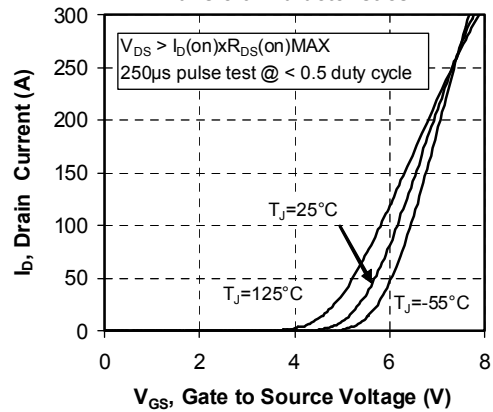
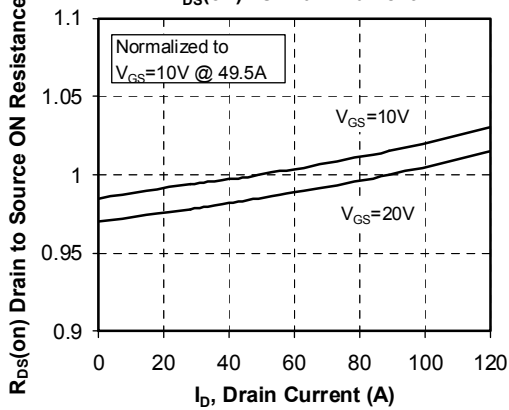
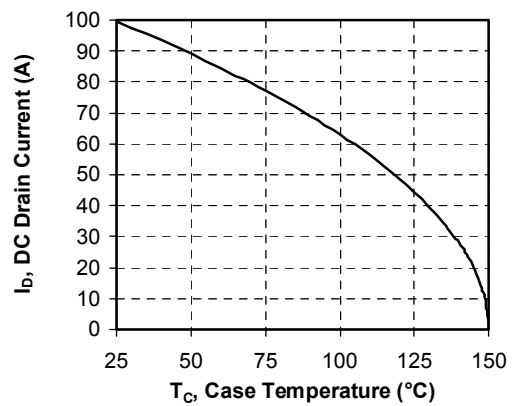
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

## SP4 Package outline (dimensions in mm)

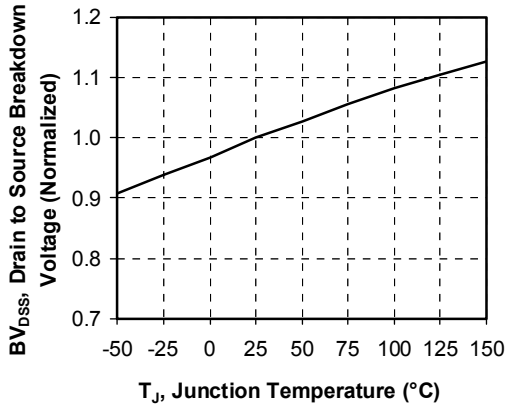


ALL DIMENSIONS MARKED "\*" ARE TOLERANCED AS:  $\pm 0.1$

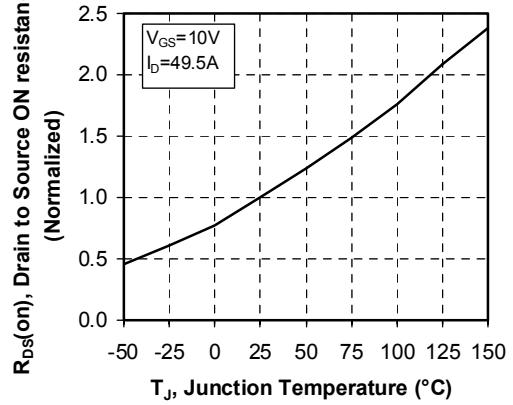
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

**Typical Performance Curve**
**Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration**

**Low Voltage Output Characteristics**

**Transfer Characteristics**

**R\_DS(on) vs Drain Current**

**DC Drain Current vs Case Temperature**


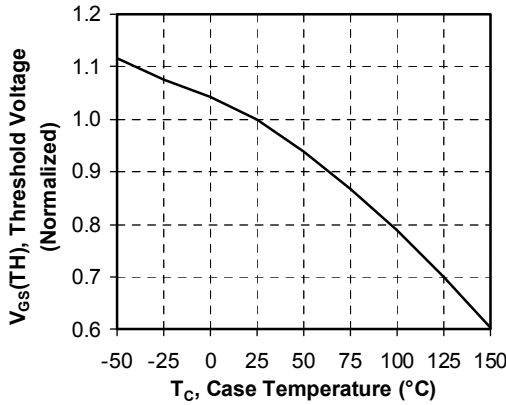
**Breakdown Voltage vs Temperature**



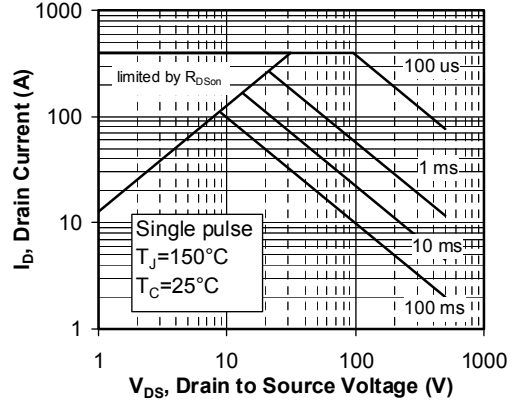
**ON resistance vs Temperature**



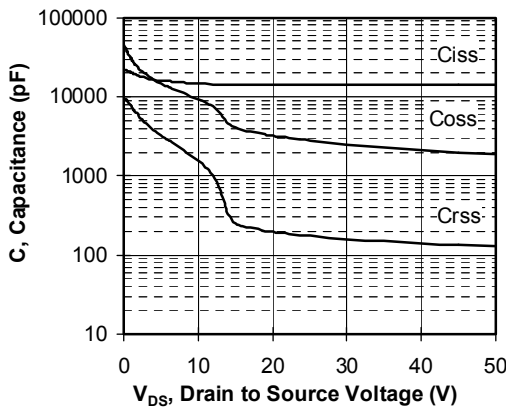
**Threshold Voltage vs Temperature**



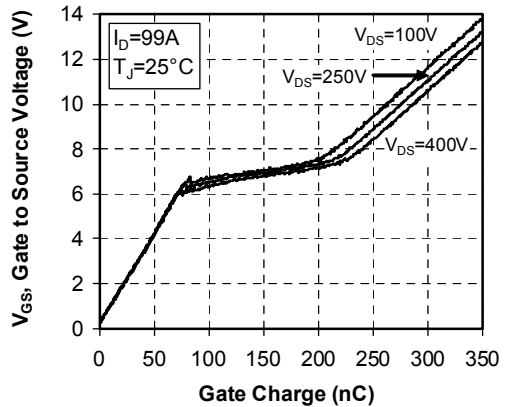
**Maximum Safe Operating Area**

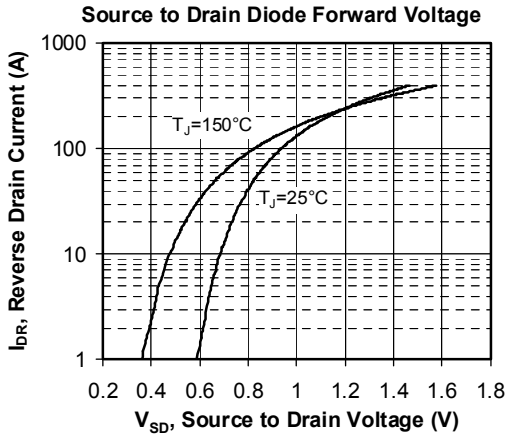
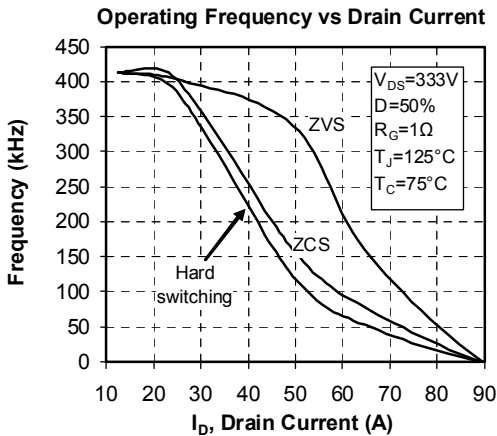
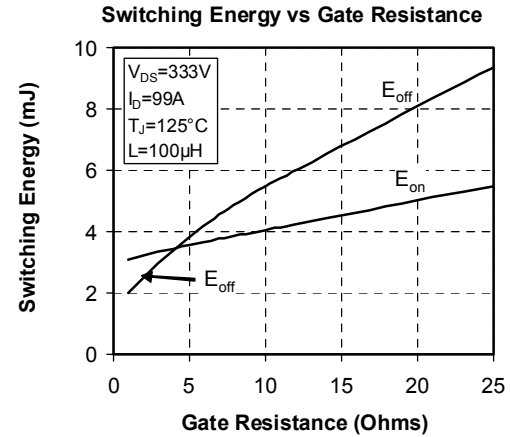
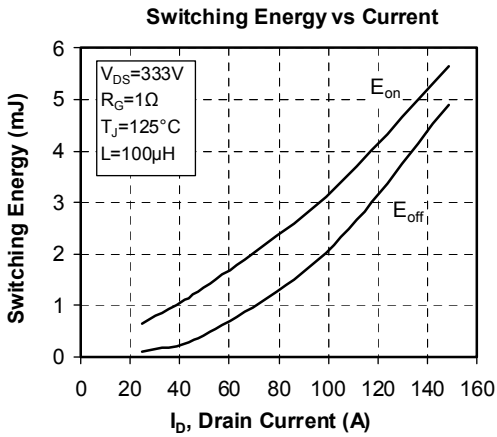
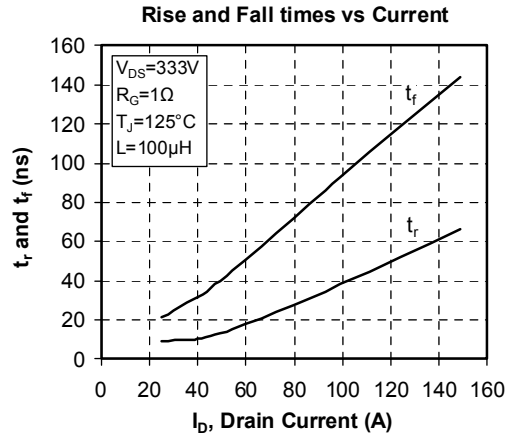
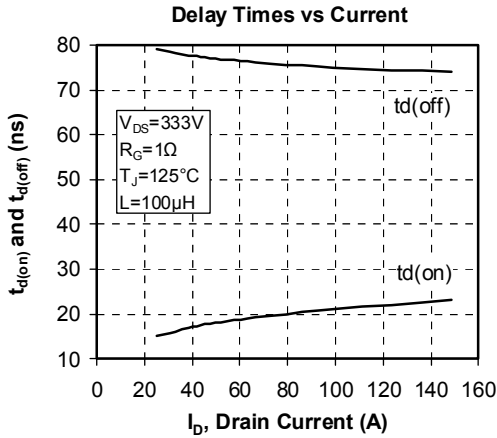


**Capacitance vs Drain to Source Voltage**



**Gate Charge vs Gate to Source Voltage**





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